

*B<sup>1</sup> Cmt* . formed and an opening including the seal member layer 64A is formed in the second photosensitive material layer 62 and the opening is stretched in a horizontal direction.

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Replace the paragraph beginning on page 29, line 21 with the following paragraph:

As shown in FIG. 24C, a sealing material layer 64B is filled in the opening 20.

Likewise, as shown in FIG. 24D, a third photosensitive material layer 66 is formed, then *B<sup>2</sup>* an opening is defined. The opening is formed in a position extended in the vertical direction of the opening as shown in FIG. 24D. The sealing member layer 64C is filled in the opening.

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Replace the paragraph beginning on page 33, line 11 with the following paragraph:

*B<sup>3</sup>* As shown in FIG. 27C and FIG. 27D, an insulating layer 85 is formed on a first temporary board 84A by a CVD or sputtering technique. Although it is preferable that the first temporary board 84A is formed of a silicon semiconductor board, it may be formed of other boards such as quartz board and the like. A thickness of insulating layer 85 is preferable to range from 0.5  $\mu\text{m}$  to 1.5  $\mu\text{m}$ .

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Replace the paragraph beginning on page 33, line 20 with the following paragraph: